

ECE 474 HW2  
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- a. Find the total area used by the alu. (report\_area command)

```

Number of ports:                60
Number of nets:                 189
Number of cells:                135
Number of combinational cells:  133
Number of sequential cells:      1
Number of macros/black boxes:    0
Number of buf/inv:              21
Number of references:           19

Combinational area:             1373.123011
Buf/Inv area:                   116.130004
Noncombinational area:          0.000000
Macro/Black Box area:           0.000000
Net Interconnect area:          66.629990

Total cell area:                1373.123011
Total area:                     1439.753001
1

```

**Total area: 1439.753001**

- b. How many different types of cells (gates) were utilized : (report\_hierarchy command)

```

alu
  AND2X1          saed90nm_typ
  AND3X1          saed90nm_typ
  AND4X1          saed90nm_typ
  A021X1          saed90nm_typ
  A022X1          saed90nm_typ
  A0221X1         saed90nm_typ
  A0222X1         saed90nm_typ
  A0I222X1        saed90nm_typ
  INVX0           saed90nm_typ
  MUX21X1         saed90nm_typ
  NAND2X0         saed90nm_typ
  NAND3X0         saed90nm_typ
  NOR2X0          saed90nm_typ
  OA21X1          saed90nm_typ
  OAI21X1         saed90nm_typ
  OR2X1           saed90nm_typ
  OR4X1           saed90nm_typ
  XOR2X1          saed90nm_typ
  alu_DW01_addsub_0
    FADDX1        saed90nm_typ
    XOR2X1        saed90nm_typ
    XOR3X1        saed90nm_typ

```

1

**Types of Cells : 21**

- c. Number of cells (gates). This will require using the report\_area command as well as looking at the cell library databook. It is located at:

/nfs/guille/a1/cadlibs/synop\_lib/SAED\_EDK90nm/Digital\_Standard\_Cell\_Library/doc/databook

Its is called SAED Digital Standard Cell Library\_Rev1\_4\_20. Its is a pdf file but has no .pdf on it. Search for the cell "NAND2X1" and record the area. (pg 34) Divide the total area reported by design\_vision by this number to get the gate equivalent count.

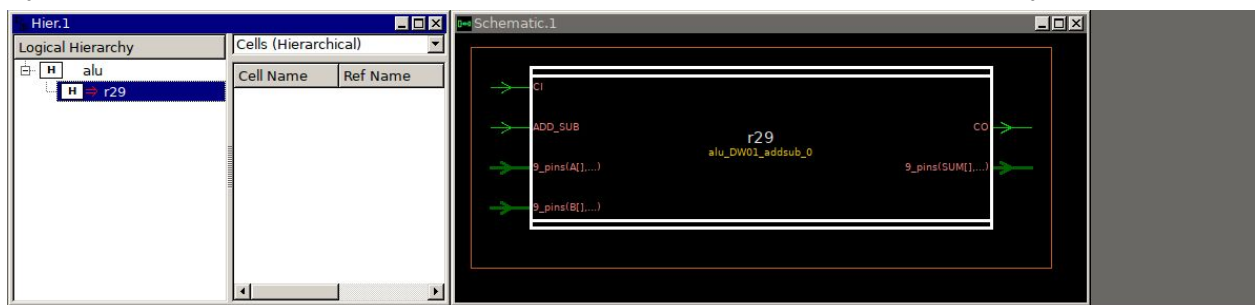
Table 9.12. NAND Electrical Parameters and Areas

Cell Name	Operating Conditions: VDD=1.2 V DC, Temp=25 Deg.C, Operating Frequency: Freq=300 MHz, Capacitive Standard Load: Csl=13 fF				Area
	Cload	Prop Delay (Avg)	Power		
			Leakage (VDD=1.32 V DC, Temp=25 Dec.C)	Dynamic	
		ps	nW	nW/MHz	
NAND2X1	1 x Csl	51	336	15	5.5296
NAND2X2	2 x Csl	51	673	28	9.2160
NAND3X1	1 x Csl	130	492	38	11.9808
NAND3X2	2 x Csl	142	770	59	12.9024
NAND4X0	0.5 x Csl	66	400	22	8.2944
NAND4X1	1 x Csl	127	716	57	12.9024

**NAND2X1: Area = 5.5296  $\mu\text{m}^2$**

Gate equivalent count= (total area)/ (area NAND2X1) = **1439.753001/5.5296=260.372**

- d. The synthesis tool will most likely introduce a hierarchical block to your design because it recognized something in your design. What is the block and what does it do? What style of implementation was chosen for this element? Hint: see report\_hierarchy output



**Block: alu\_DW01\_addsub\_0 ,which is an adder.**

**Style: adder**

- e. What was the maximum delay path through the alu and what were the beginning and endpoints for the max delay path?: (report\_timing command)

-----		
input external delay	0.00	0.00 f
opcode[0] (in)	0.00	0.00 f
U162/QN (INVX0)	0.19	0.19 r
U233/QN (NAND2X0)	0.18	0.36 f
U223/Q (0A21X1)	0.24	0.61 f
U222/Q (0R2X1)	0.09	0.70 f
U220/QN (NAND3X0)	0.05	0.74 r
r29/B[0] (alu_DW01_addsub_0)	0.00	0.74 r
r29/U8/Q (X0R2X1)	0.15	0.90 r
r29/U1_0/C0 (FADDX1)	0.15	1.04 r
r29/U1_1/C0 (FADDX1)	0.13	1.18 r
r29/U1_2/C0 (FADDX1)	0.13	1.31 r
r29/U1_3/C0 (FADDX1)	0.13	1.44 r
r29/U1_4/C0 (FADDX1)	0.13	1.57 r
r29/U1_5/C0 (FADDX1)	0.13	1.70 r
r29/U1_6/C0 (FADDX1)	0.13	1.84 r
r29/U1_7/S (FADDX1)	0.20	2.03 f
r29/SUM[7] (alu_DW01_addsub_0)	0.00	2.03 f
U204/QN (A0I222X1)	0.23	2.27 r
U206/QN (NAND2X0)	0.08	2.35 f
U211/Q (0R4X1)	0.14	2.49 f
U209/QN (N0R2X0)	0.04	2.53 r
alu_zero (out)	0.00	2.53 r
data arrival time		2.53
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(Path is unconstrained)		

**Max delay path=2.53**

**Beginning point:opcode[0] (in)**

**End point: alu\_zero (out)**

Schematic of your synthesized alu

